

NVD5117PL

MOSFET – Power, Single, P-Channel

-60 V, 16 mΩ, -61 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- High Current Capability
- Avalanche Energy Specified
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	-60	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	-61	A
		$T_C = 100^\circ\text{C}$	-43	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	118	W
		$T_C = 100^\circ\text{C}$	59	
Continuous Drain Current $R_{\theta JA}$ (Notes 1 & 2)	Steady State	$T_A = 25^\circ\text{C}$	-11	A
		$T_A = 100^\circ\text{C}$	-8	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	Steady State	$T_A = 25^\circ\text{C}$	4.1	W
		$T_A = 100^\circ\text{C}$	2.1	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	-419	A
Current Limited by Package (Note 3)	$T_A = 25^\circ\text{C}$	$I_{Dmaxpkg}$	60	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	-118	A	
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{L(pk)} = 40 \text{ A}, L = 0.3 \text{ mH}, R_G = 25 \Omega$)	E_{AS}	240	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Drain)	$R_{\theta JC}$	1.3	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	37	

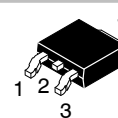
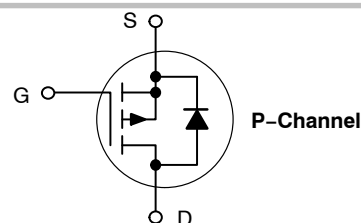
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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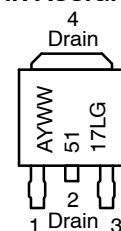
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$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
-60 V	16 mΩ @ -10 V	-61 A
	22 mΩ @ -4.5 V	



**DPAK
CASE 369C
STYLE 2**

MARKING DIAGRAMS & PIN ASSIGNMENT



1 Drain 3
Gate Source
A = Assembly Location*
Y = Year
WW = Work Week
5117L = Device Code
G = Pb-Free Package

* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejector pin), the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping†
NVD5117PLT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NVD5117PLT4G-VF01	DPAK (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVD5117PL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -60 V	T _J = 25°C		-1.0	μA
			T _J = 125°C		-100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-1.5		-2.5	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -10 V, I _D = -29 A		12	16	mΩ
		V _{GS} = -4.5 V, I _D = -29 A		16	22	
Forward Transconductance	g _{FS}	V _{DS} = -15 V, I _D = -15 A		30		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = -25 V		4800		pF
Output Capacitance	C _{oss}			480		
Reverse Transfer Capacitance	C _{rss}			320		
Total Gate Charge	Q _{G(TOT)}	V _{DS} = -48 V, I _D = -29 A	V _{GS} = -4.5 V	49		nC
			V _{GS} = -10 V	85		
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = -4.5 V, V _{DS} = -48 V, I _D = -29 A		3		V
Gate-to-Source Charge	Q _{GS}			13		
Gate-to-Drain Charge	Q _{GD}			28		
Plateau Voltage	V _{GP}			3.2		

SWITCHING CHARACTERISTICS (Notes 4)

Turn-On Delay Time	t _{d(on)}	V _{GS} = -4.5 V, V _{DS} = -48 V, I _D = -29 A, R _G = 2.5 Ω		22		ns
Rise Time	t _r			195		
Turn-Off Delay Time	t _{d(off)}			50		
Fall Time	t _f			132		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -29 A	T _J = 25°C	-0.86	-1.0	V
			T _J = 125°C	-0.74		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, di/dt = 100 A/μs, I _S = -29 A		36		ns
Charge Time	t _a			19		
Discharge Time	t _b			17		
Reverse Recovery Charge	Q _{RR}			44		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

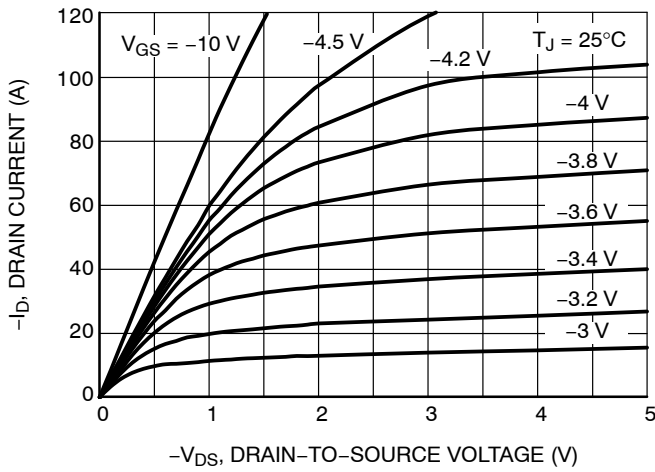


Figure 1. On-Region Characteristics

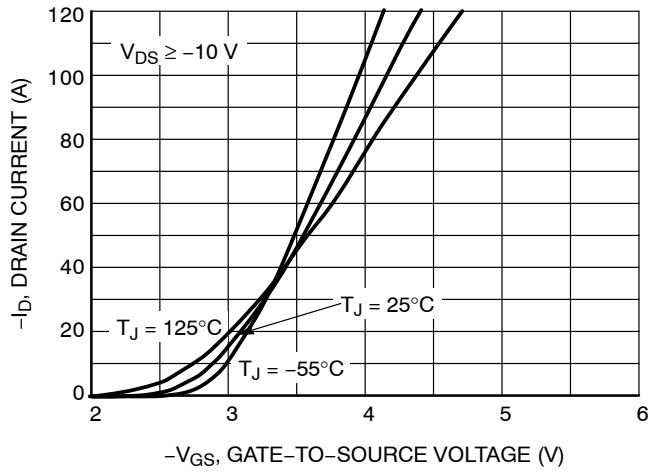


Figure 2. Transfer Characteristics

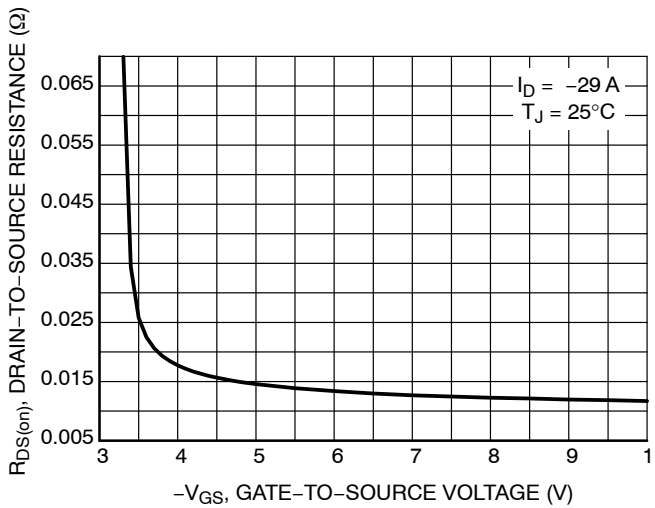


Figure 3. On-Resistance vs. Gate-to-Source Voltage

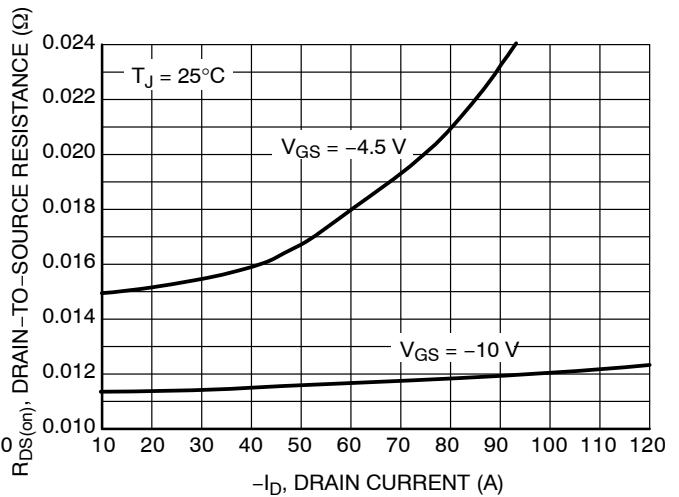


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

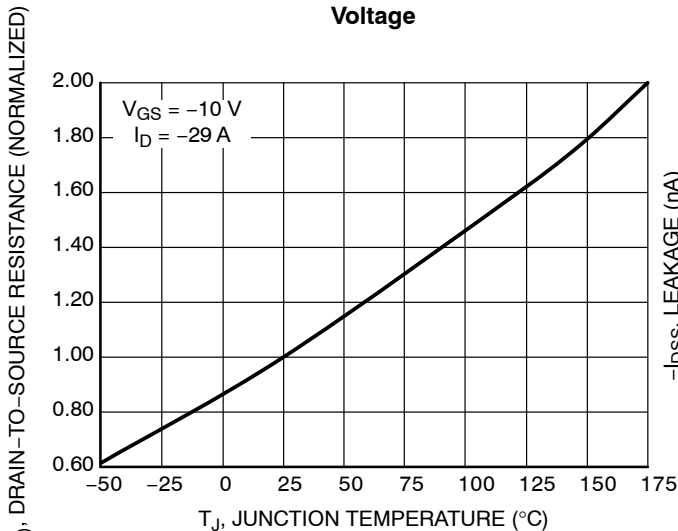


Figure 5. On-Resistance Variation with Temperature

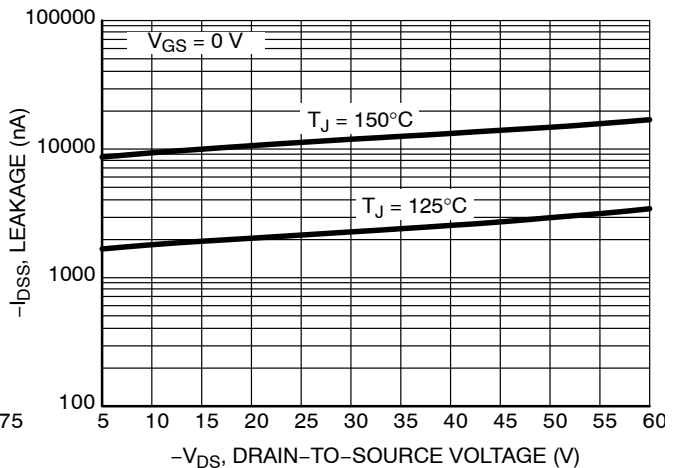


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NVD5117PL

TYPICAL CHARACTERISTICS

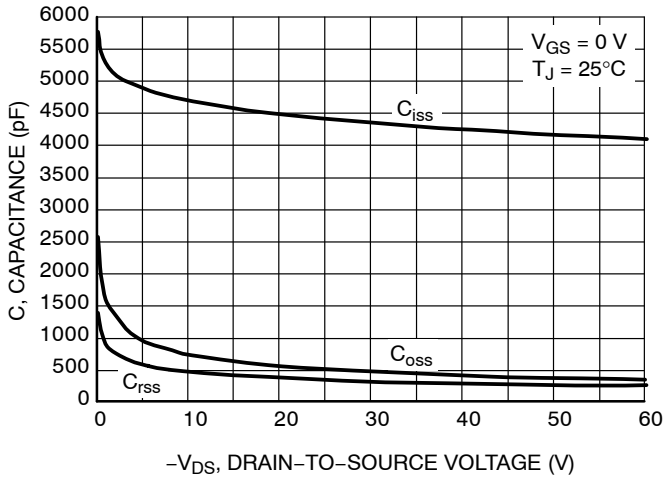


Figure 7. Capacitance Variation

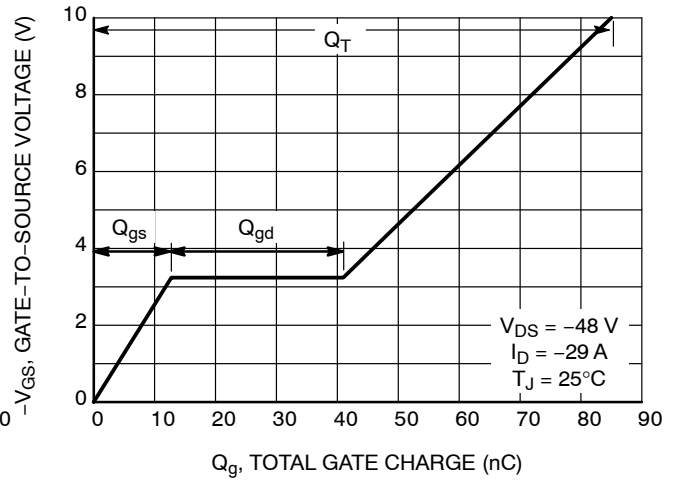


Figure 8. Gate-to-Source vs. Total Charge

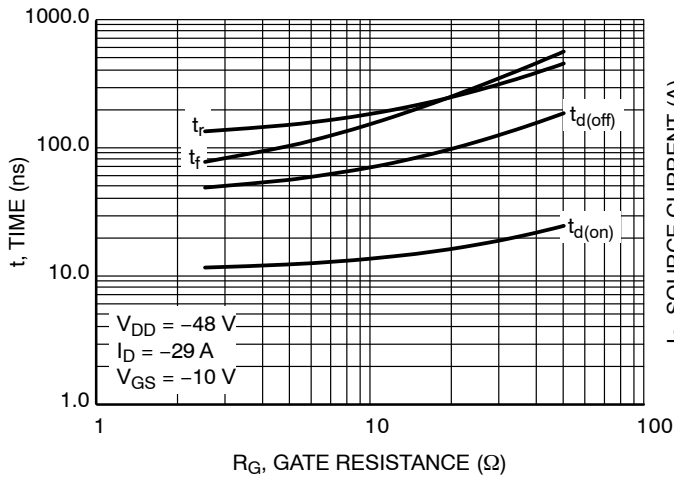


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

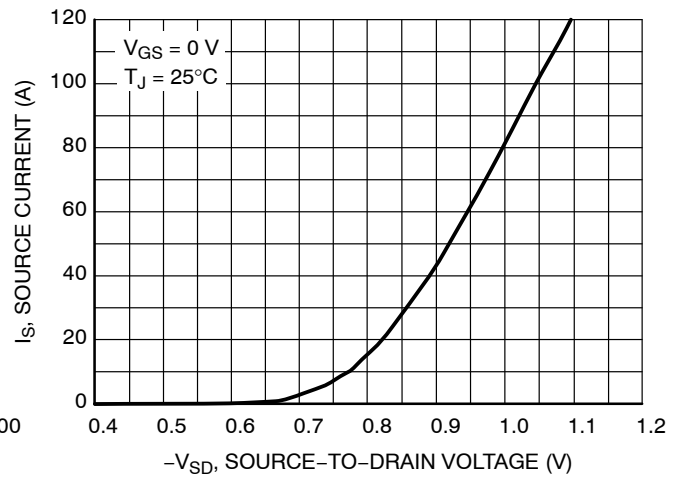


Figure 10. Diode Forward Voltage vs. Current

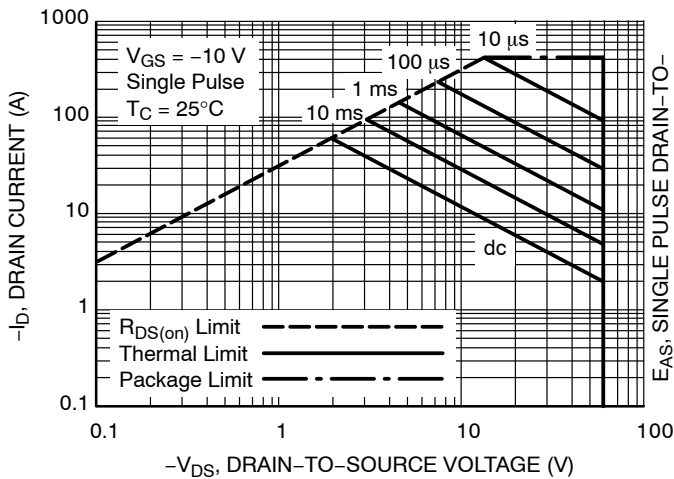


Figure 11. Maximum Rated Forward Biased Safe Operating Area

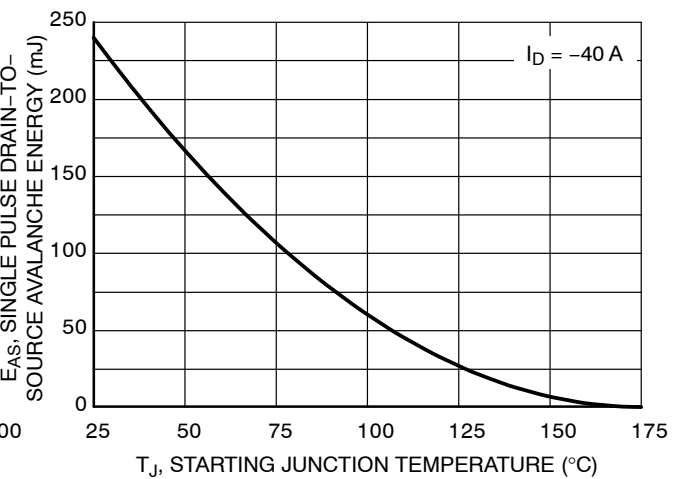


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NVD5117PL

TYPICAL CHARACTERISTICS

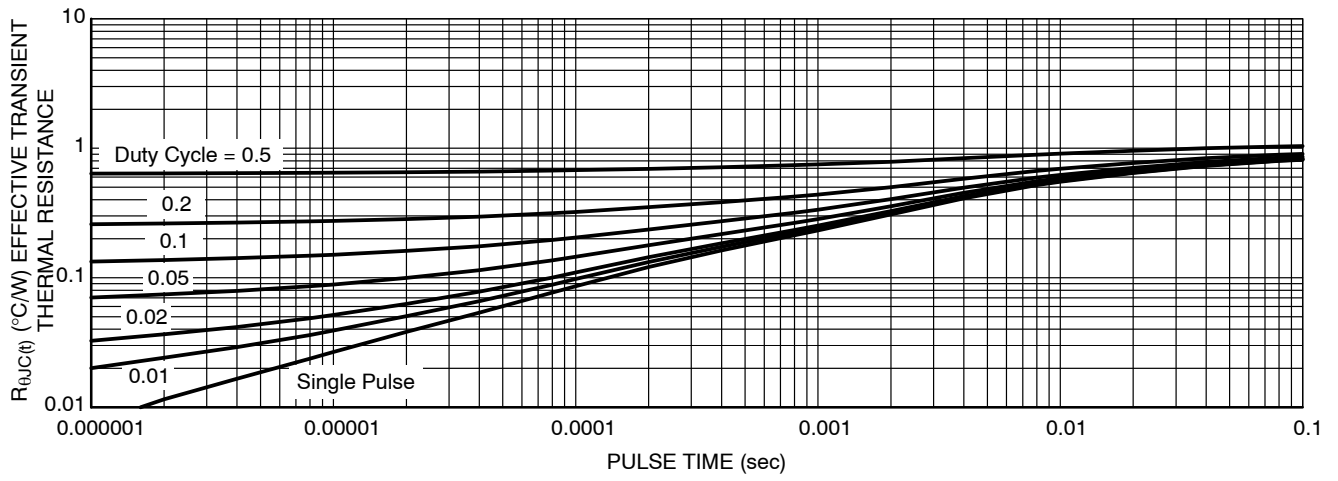


Figure 13. Thermal Response

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